

Fig. 1

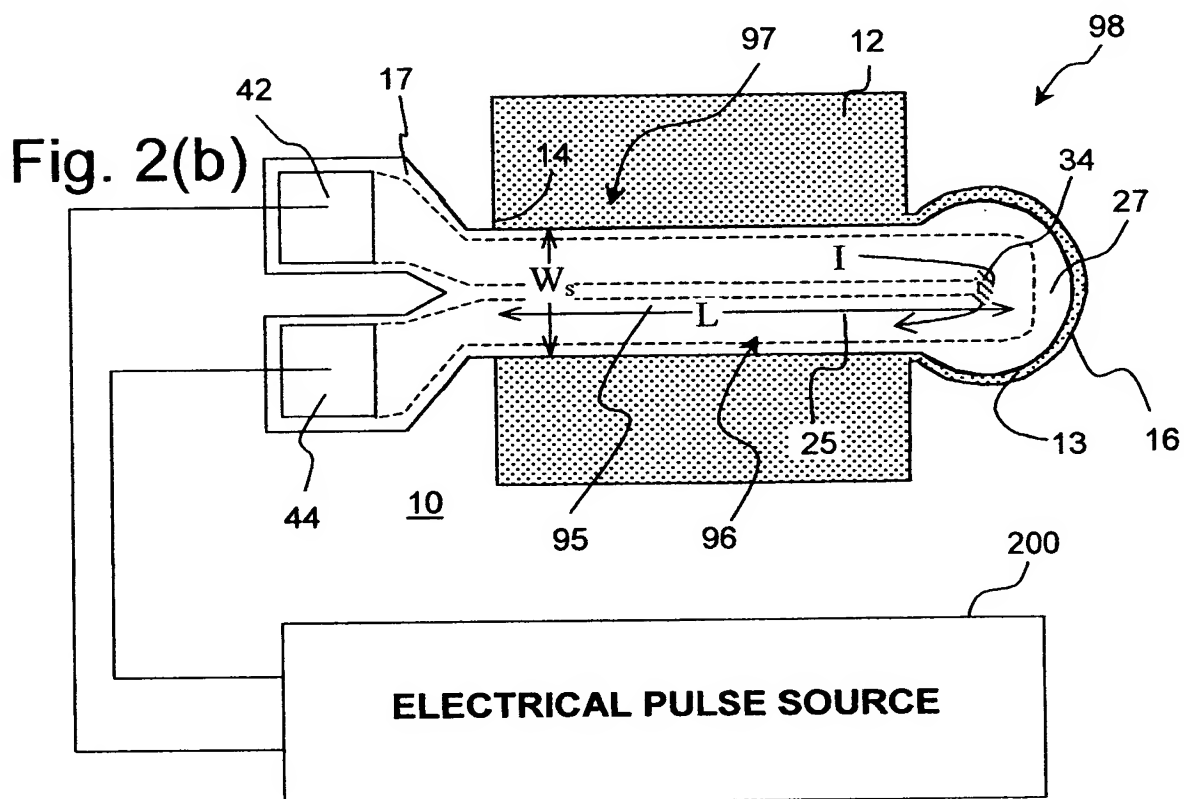
[illegible]

Fig. 3(a)

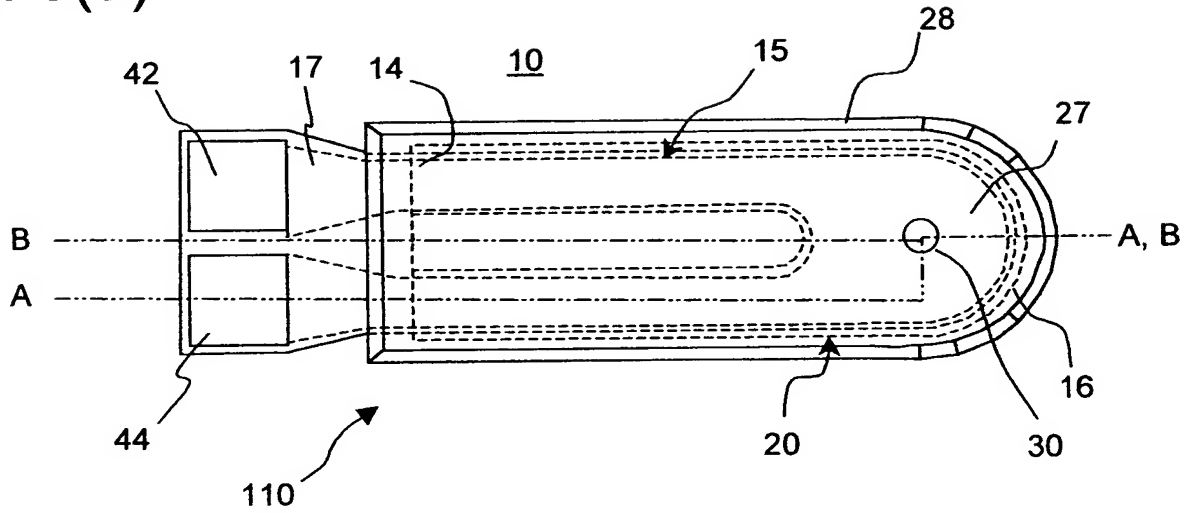
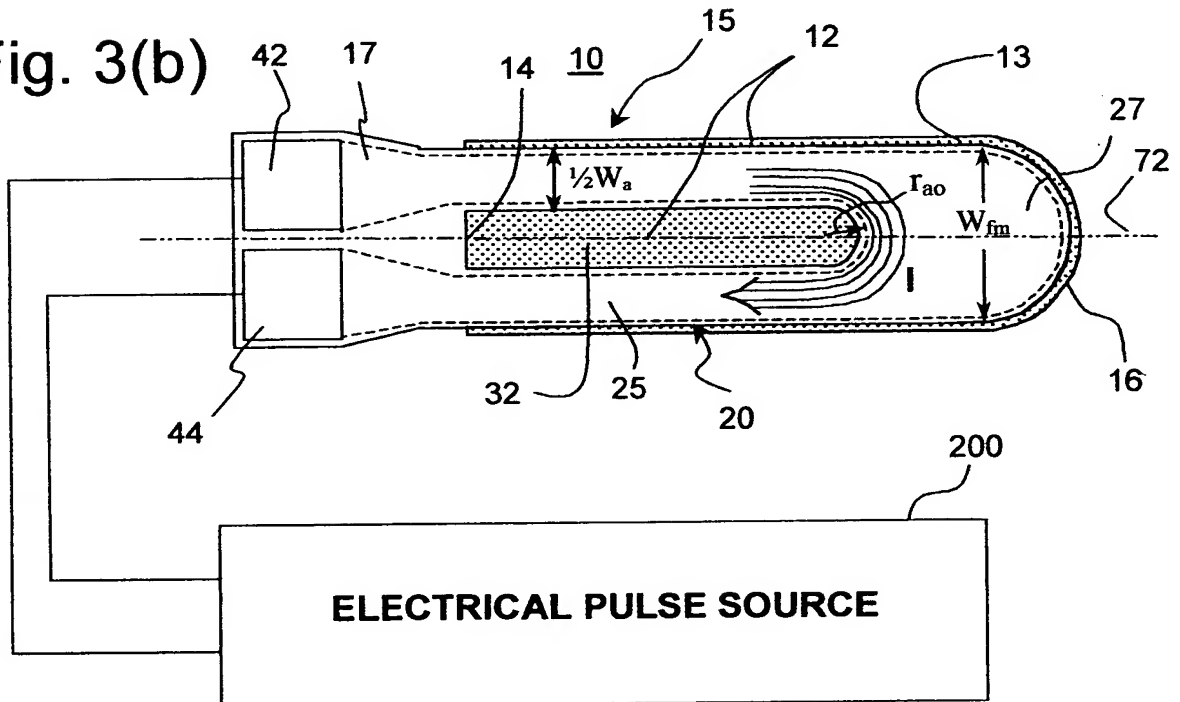


Fig. 3(b)



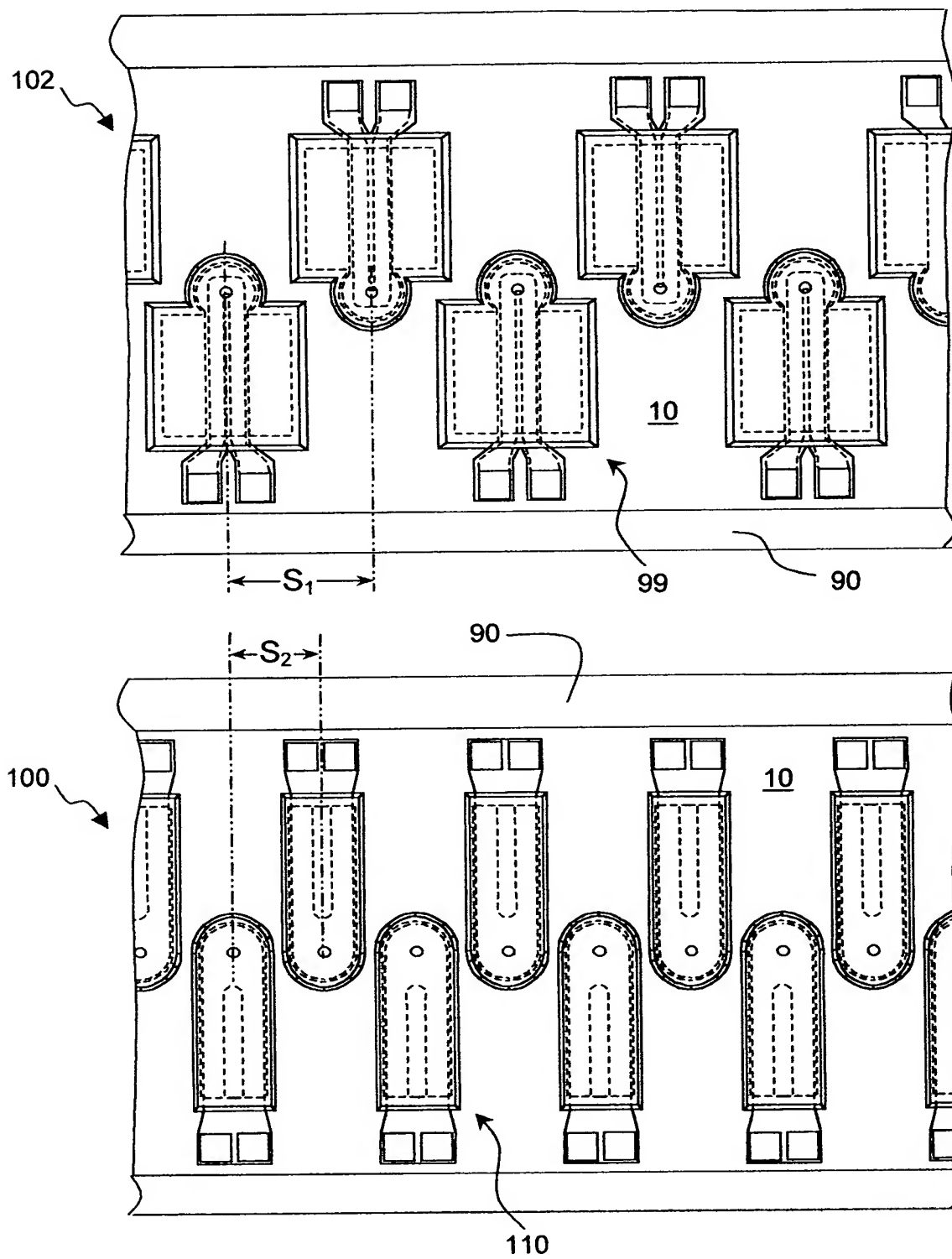


Fig. 4

Fig. 5(a)

A cross-sectional view of a semiconductor device 110. The device features a substrate 10 with a base layer 12. A central region 22 is defined by a patterned layer 24. Above this, a layer 26 is formed, which is part of a larger structure 20. A top layer 28 is also present. On the left, a contact structure 41 is shown, consisting of a base 43 and a top layer 41. A side layer 30 is located on the right, with a top surface 52. The entire structure is labeled 110.

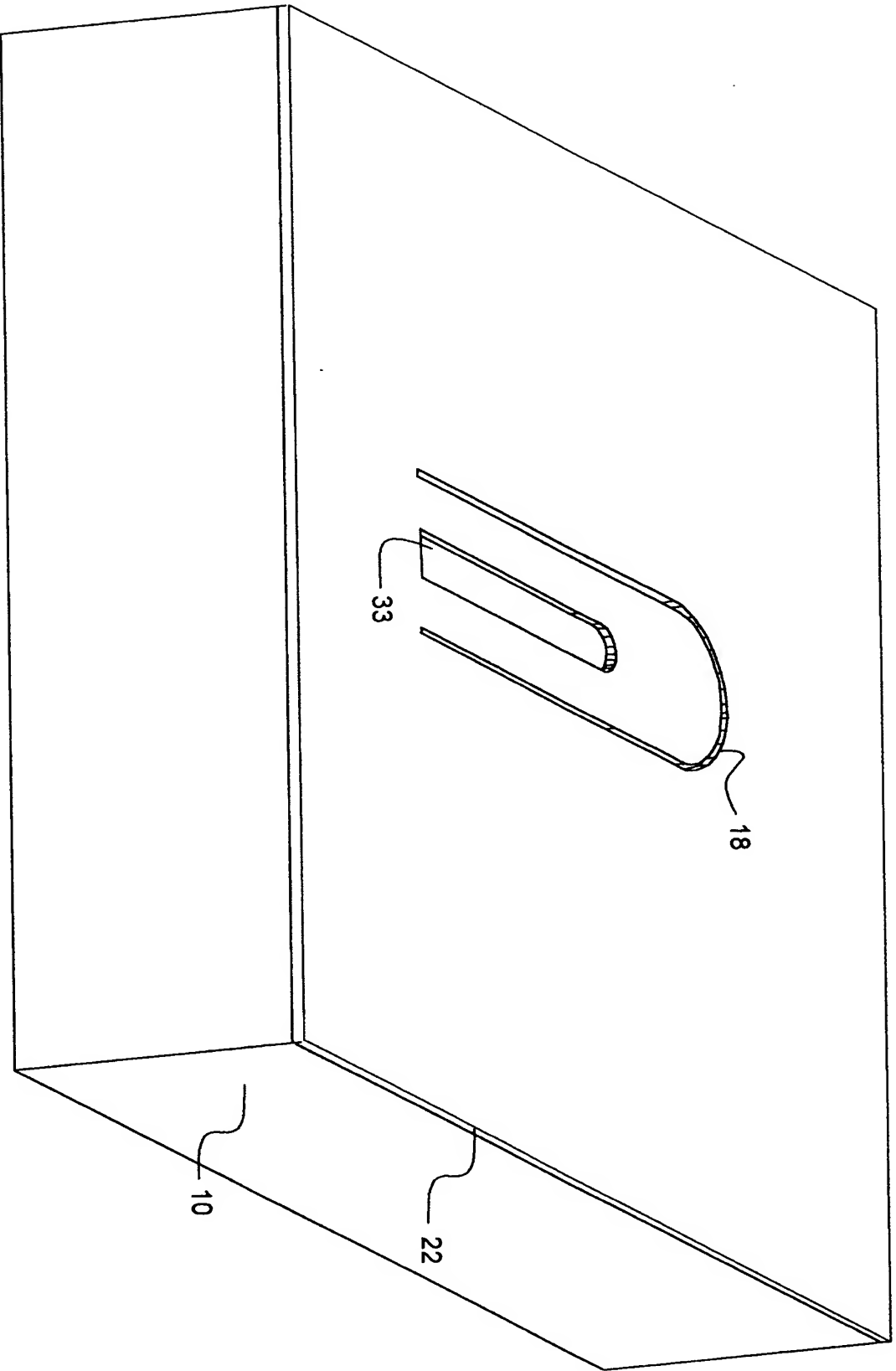


Fig. 6

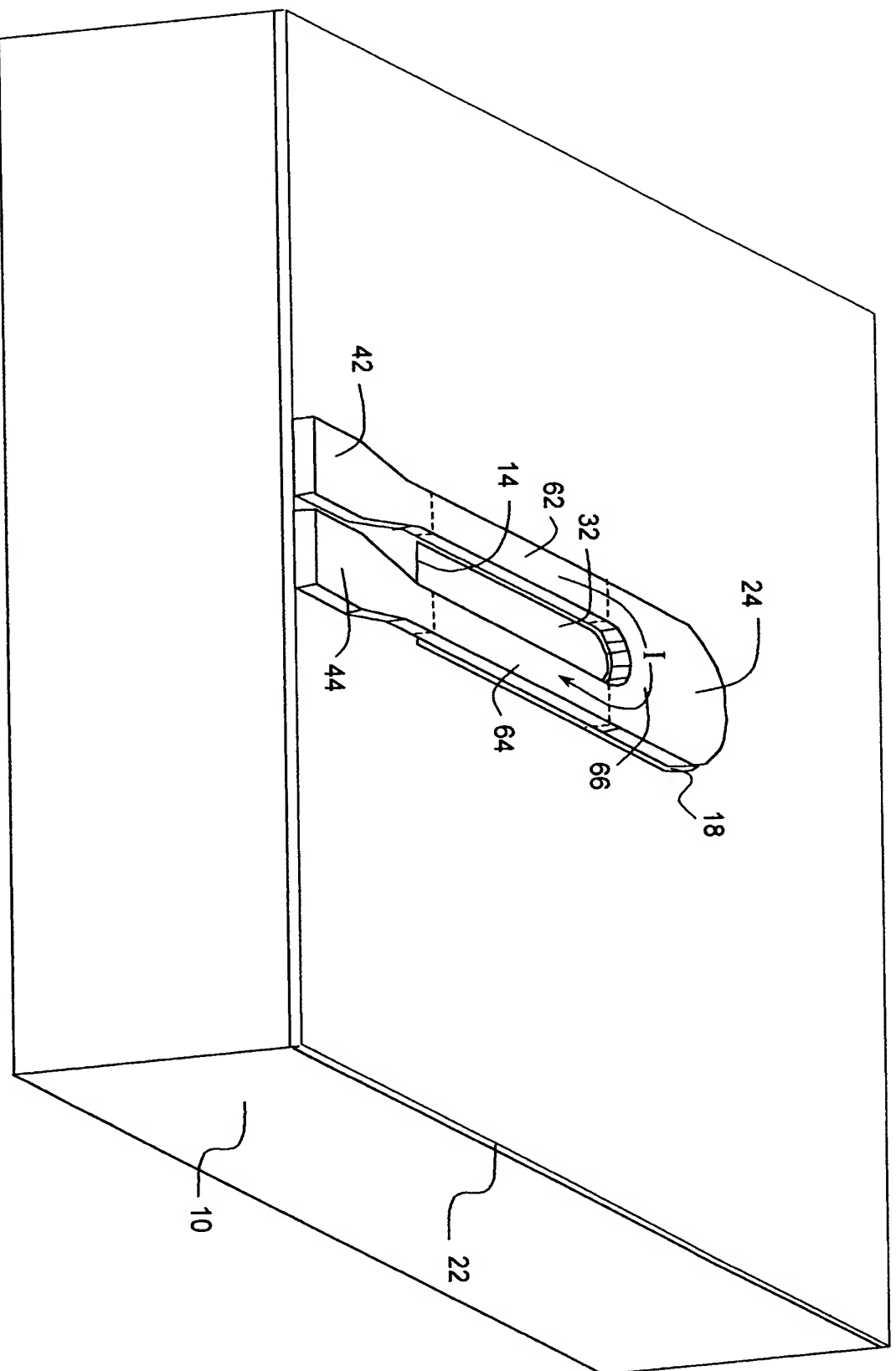


Fig. 7

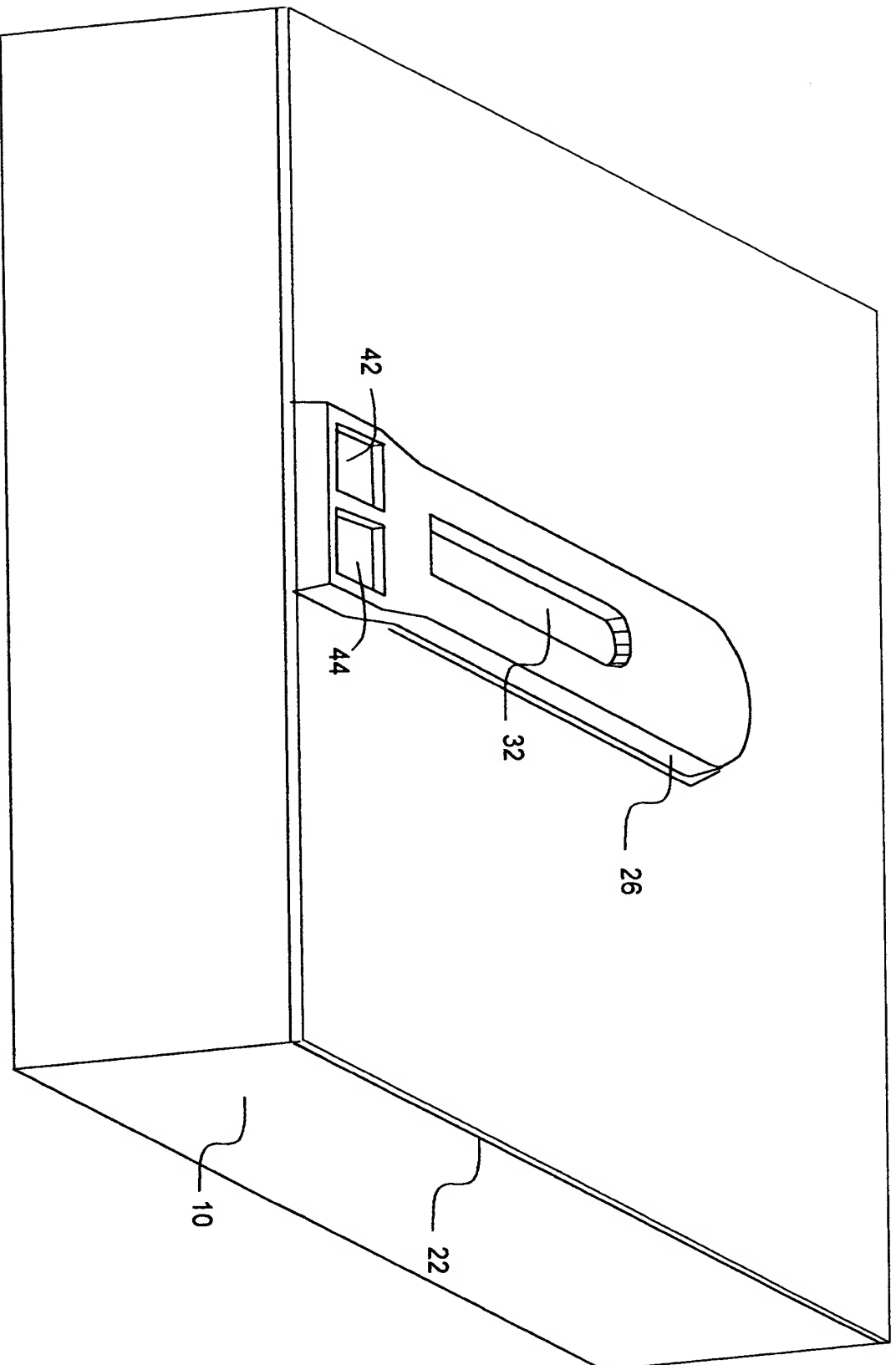


Fig. 8

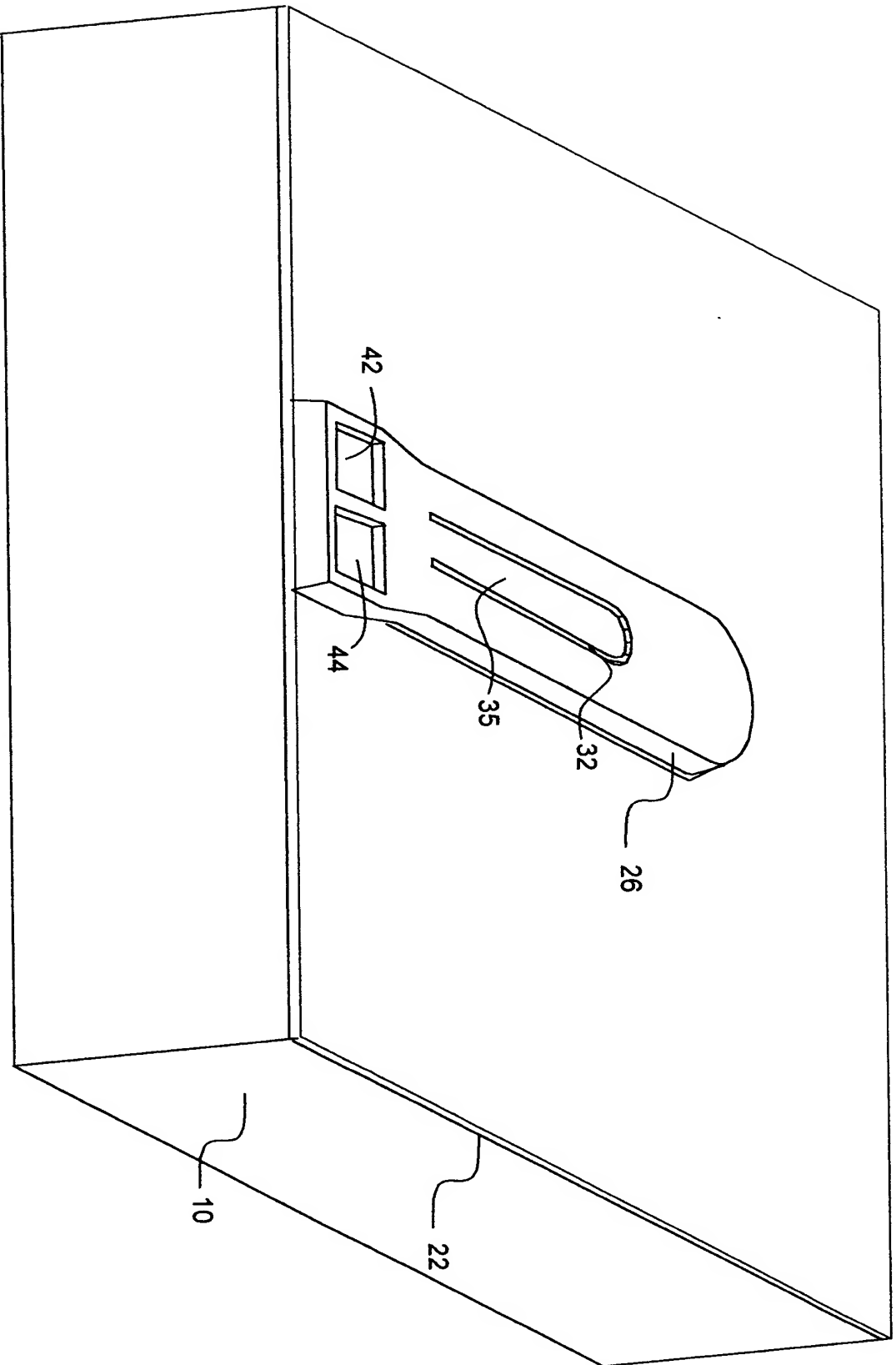


Fig. 9

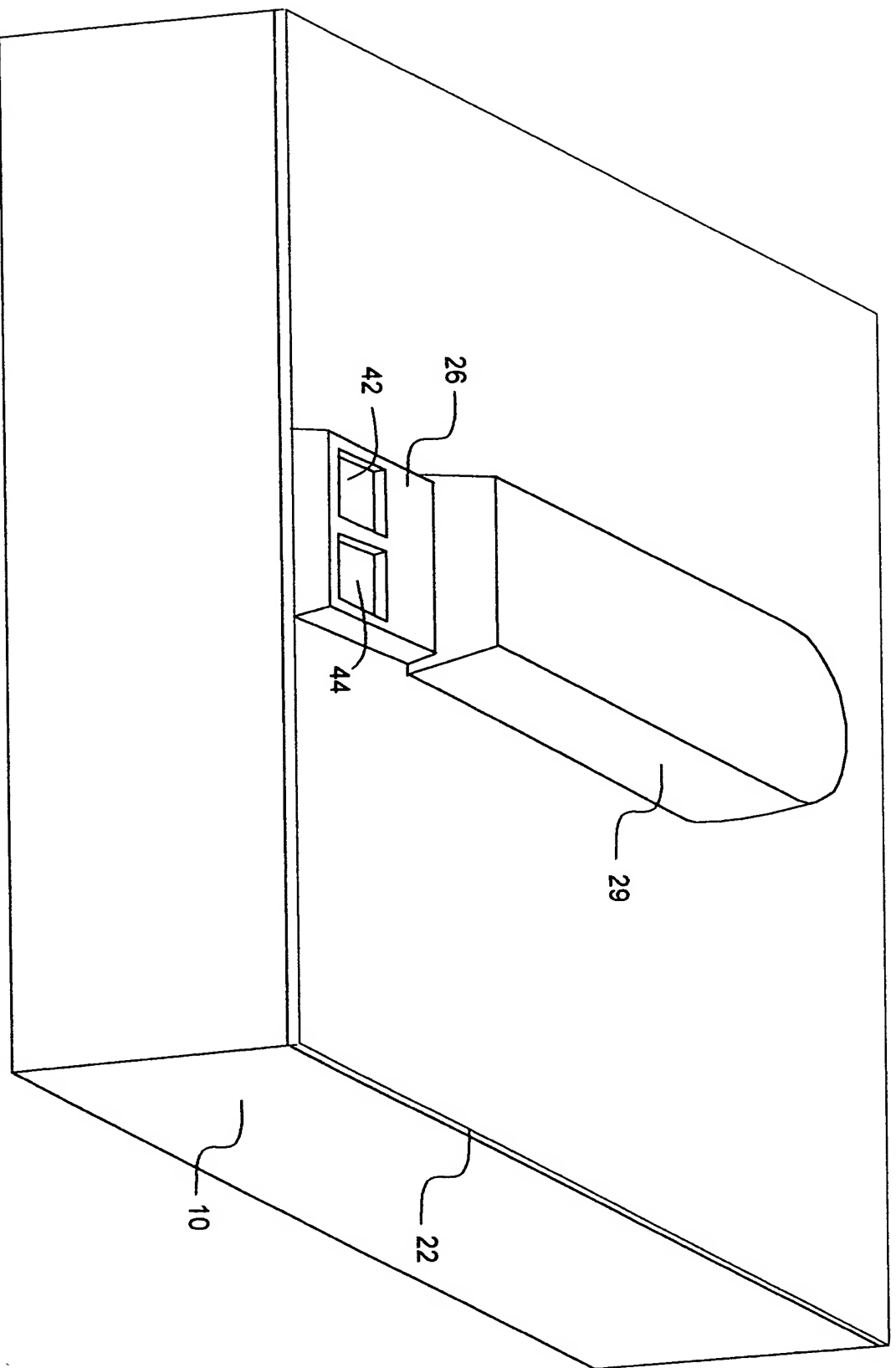


Fig. 10

Fig. 11

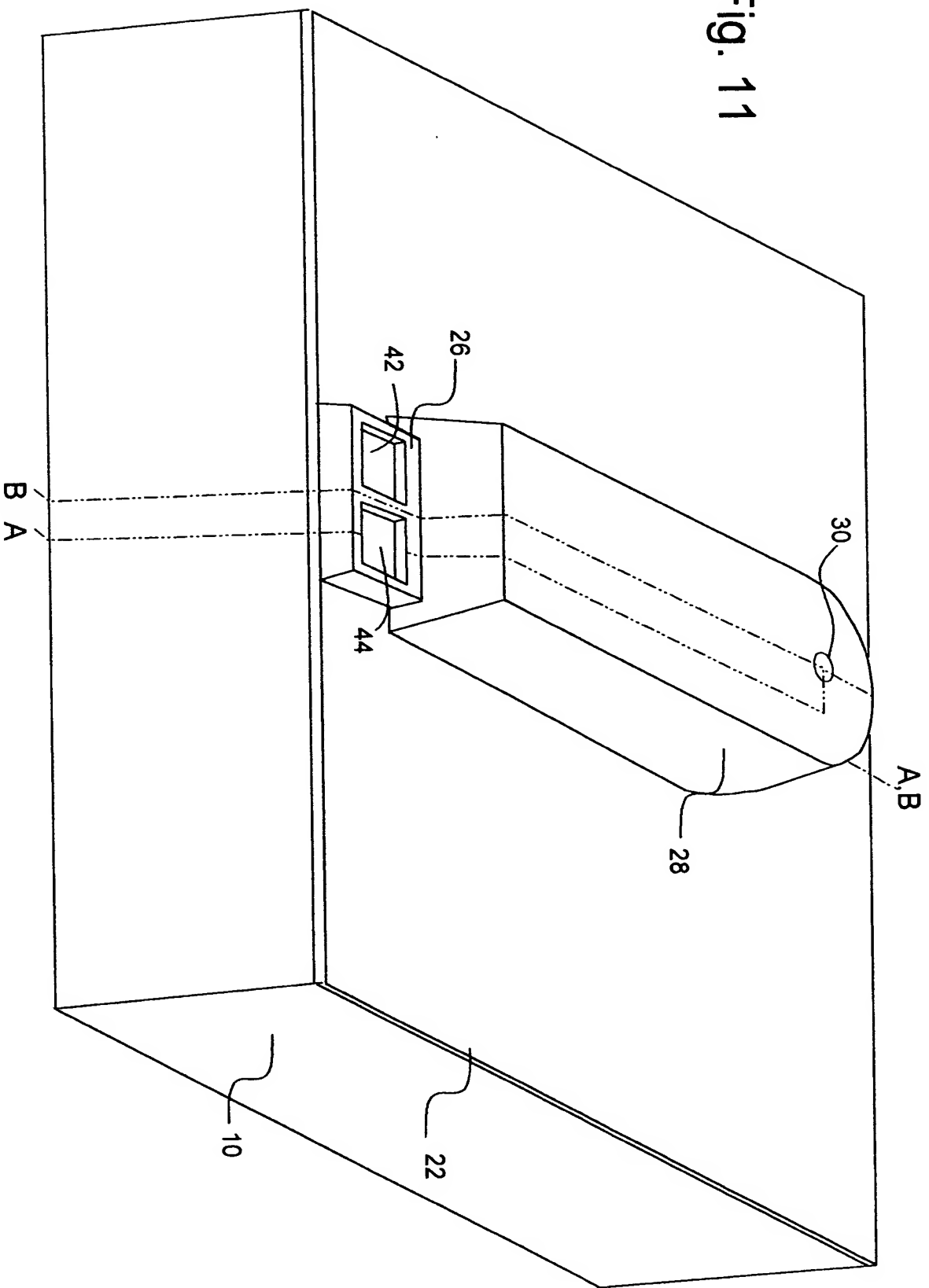


Fig. 12(a)

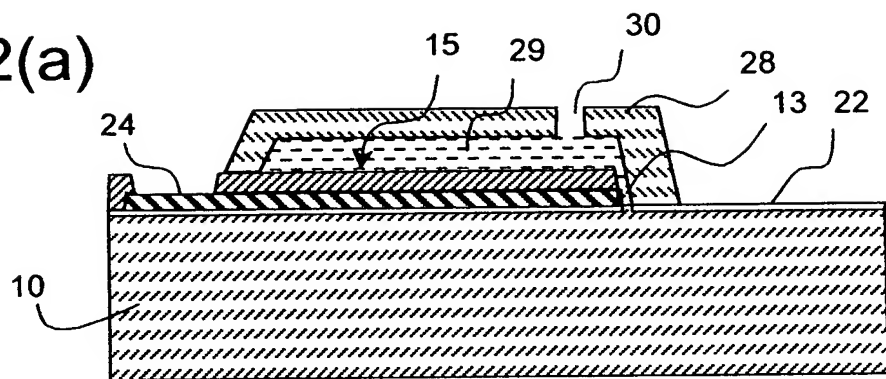


Fig. 12(b)

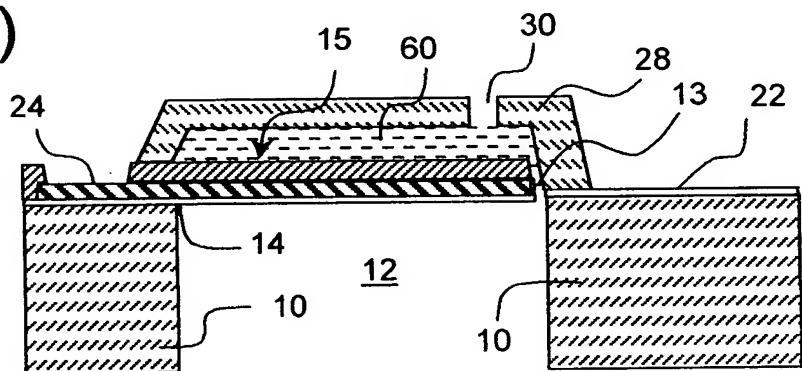


Fig. 12(c)

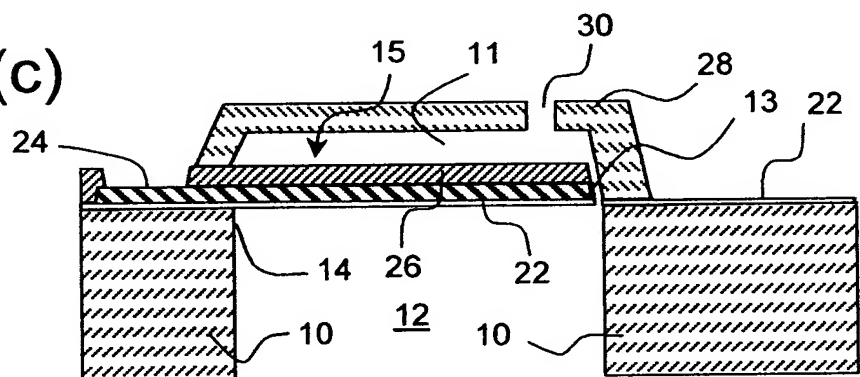


Fig. 12(d)

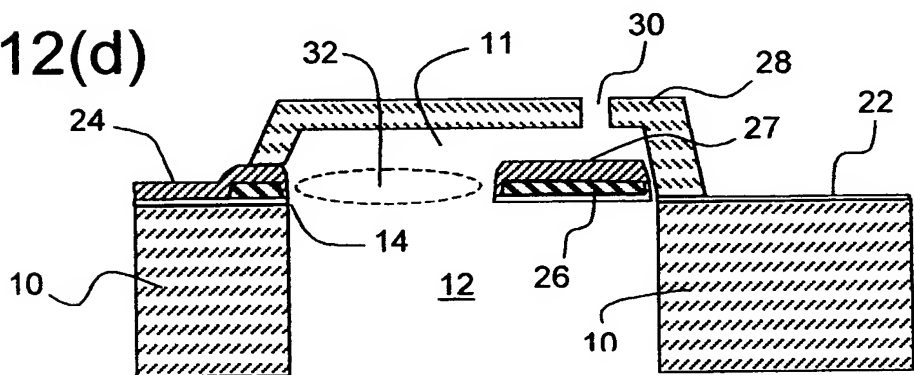


Fig. 13

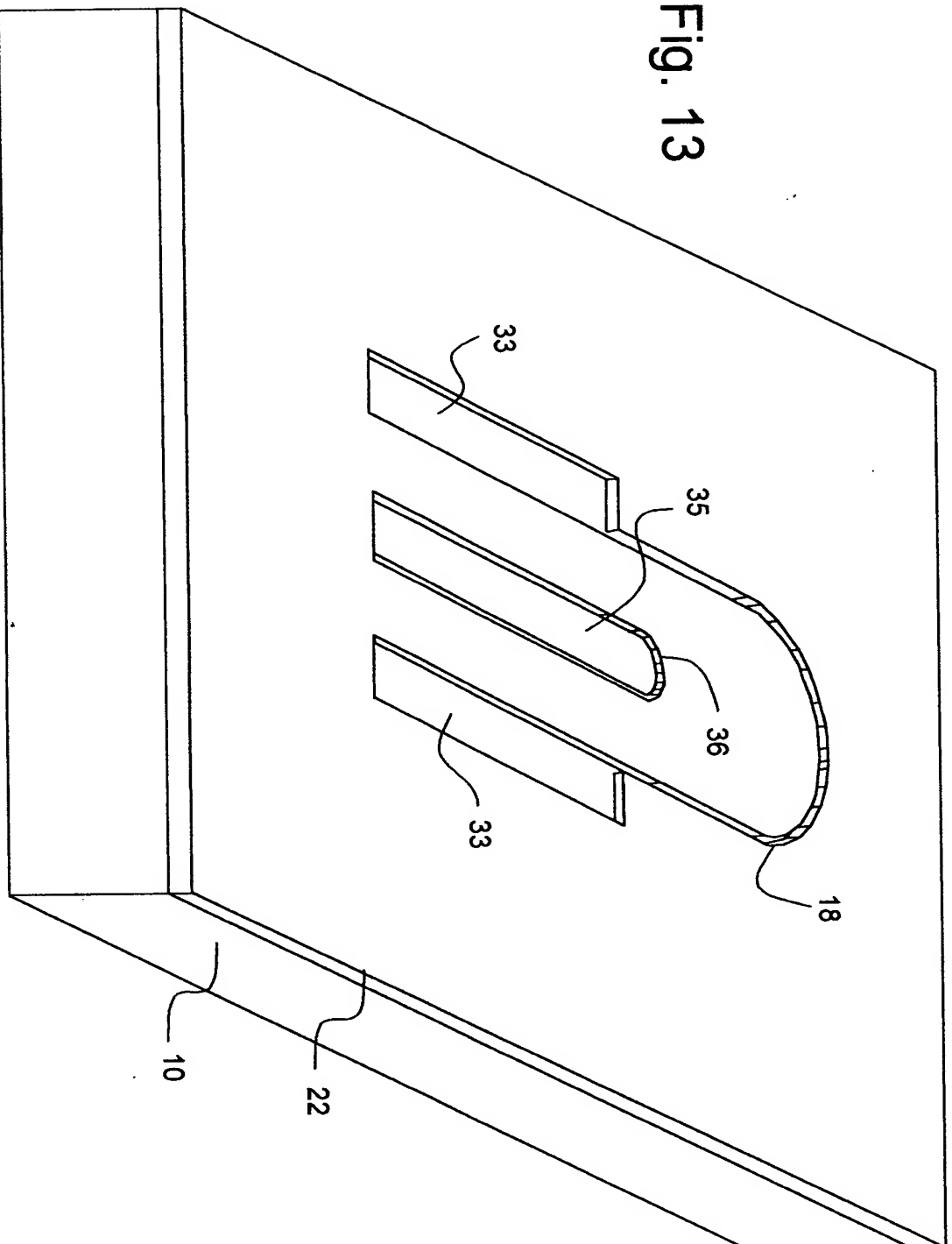


Fig. 14

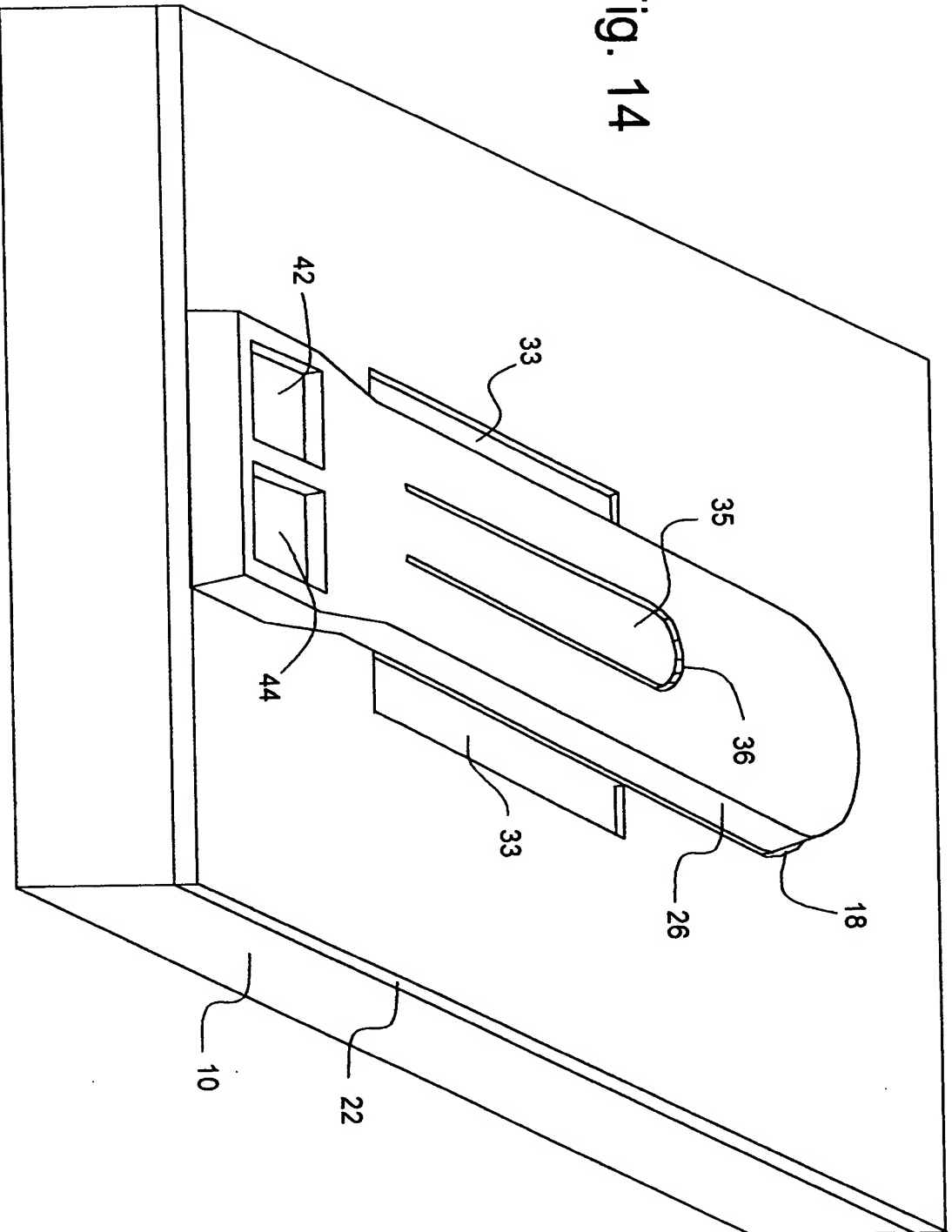


Fig. 15

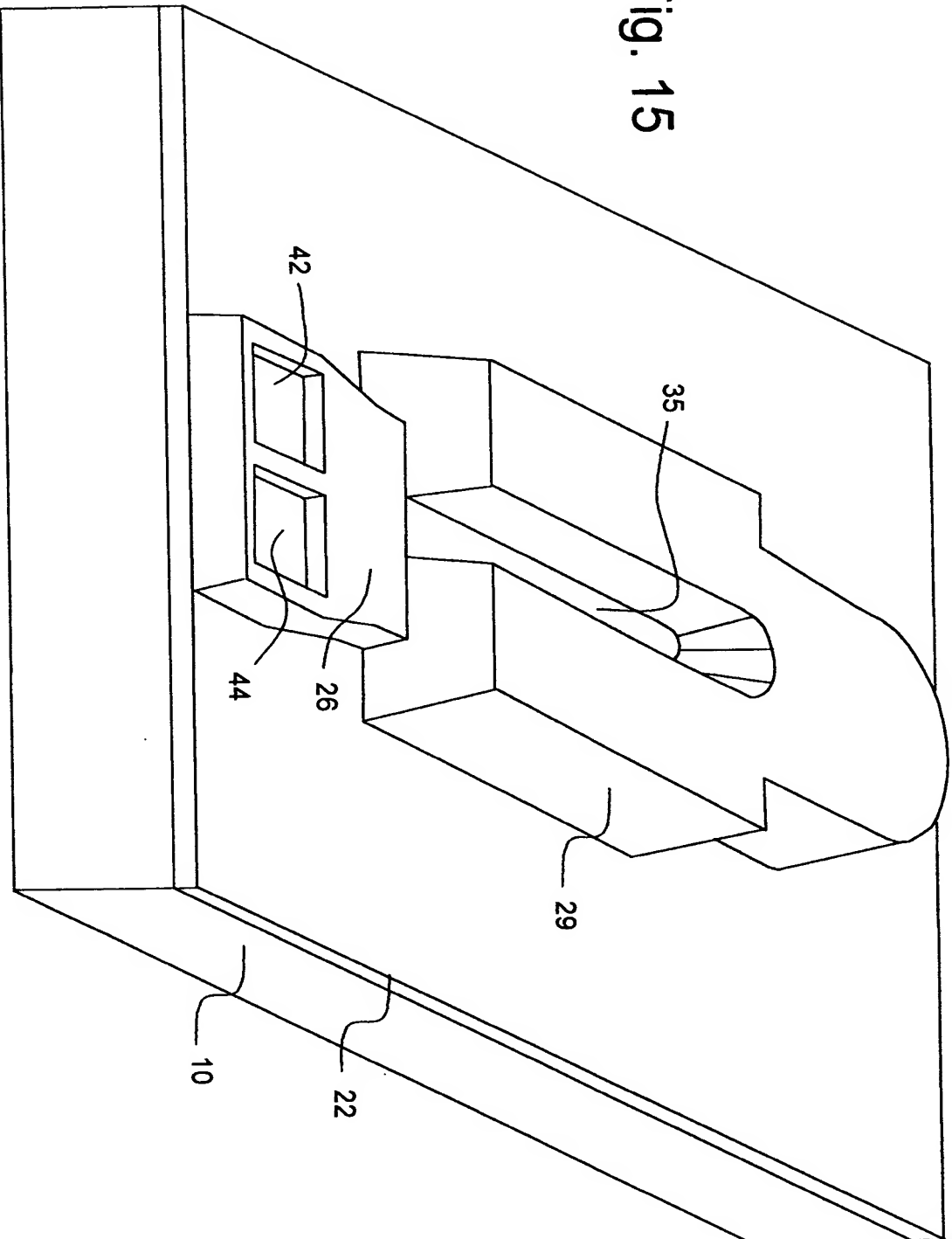


Fig. 16

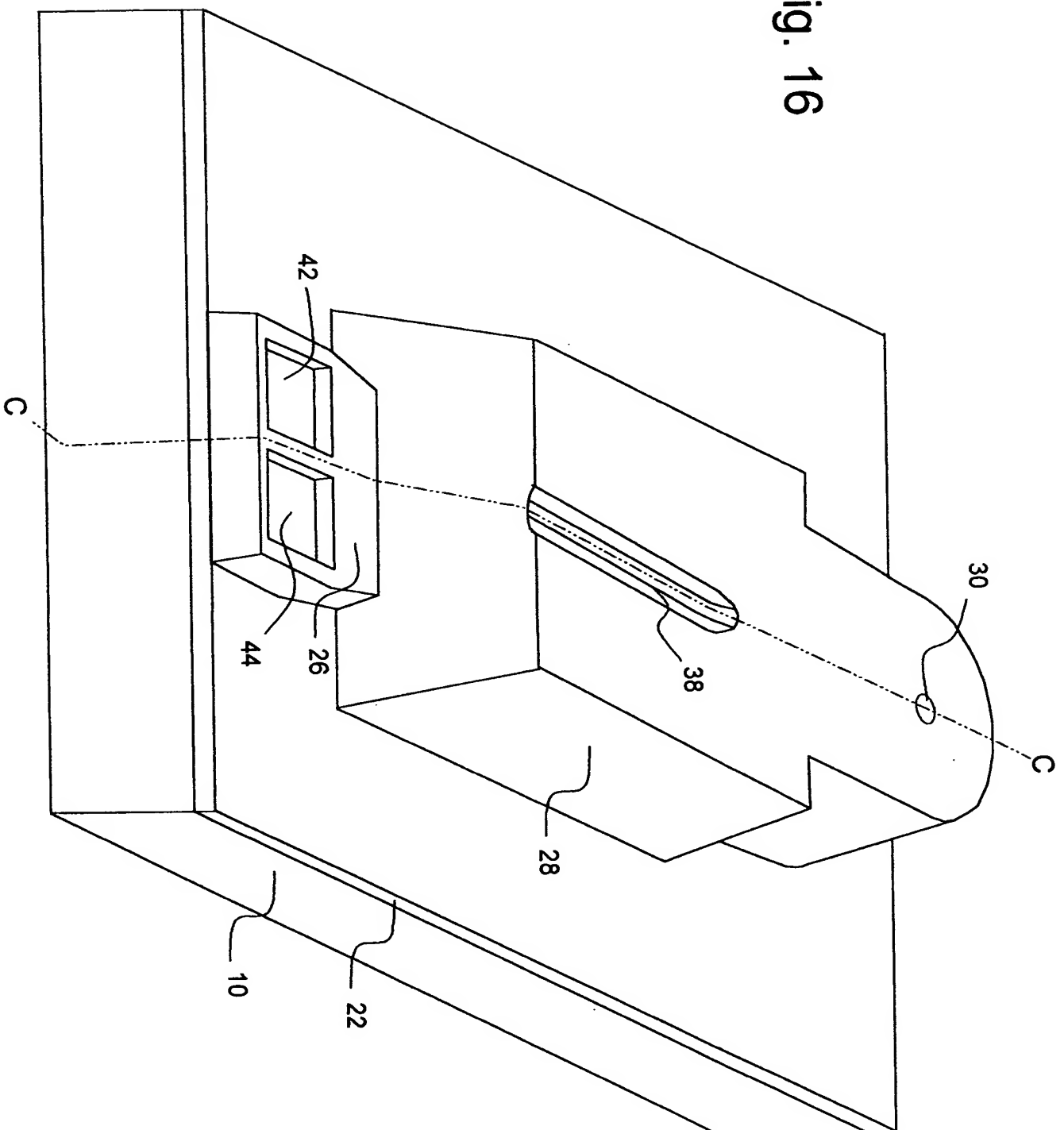


Fig. 17

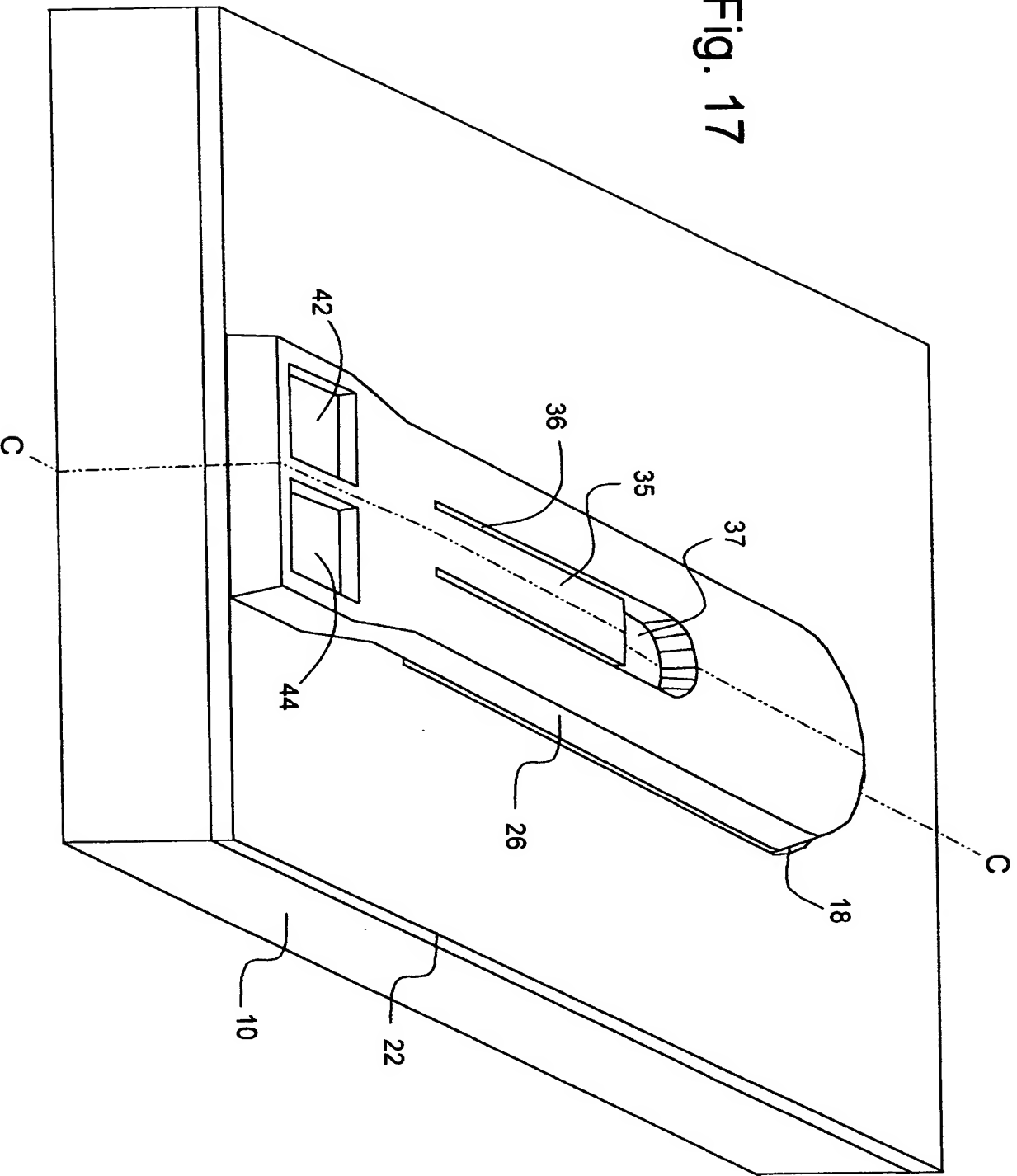


Fig. 19(a)

Fig. 19(a) is a cross-sectional view of a device 10. The device has a central elongated body 70. Within this body, there are two elongated regions 74 and 75, which are defined by dashed lines. A small circular feature 77 is located on the central body 70. The device is terminated at both ends by rectangular blocks 42 and 44. A dashed line A-A passes through the center of the device, and a solid line B-B is shown above it. Various reference numerals are used: 28, 71, 74, 30, 70, 85, 120, 44, 42, 78, 10, 77, 75, 71, 79.

Fig. 20(a)

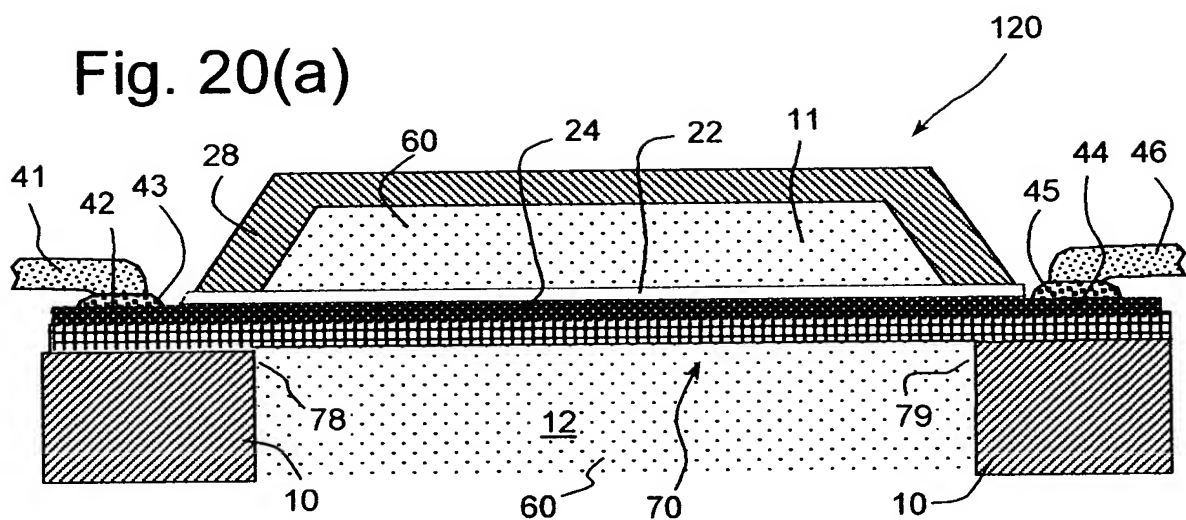


Fig. 20(b)

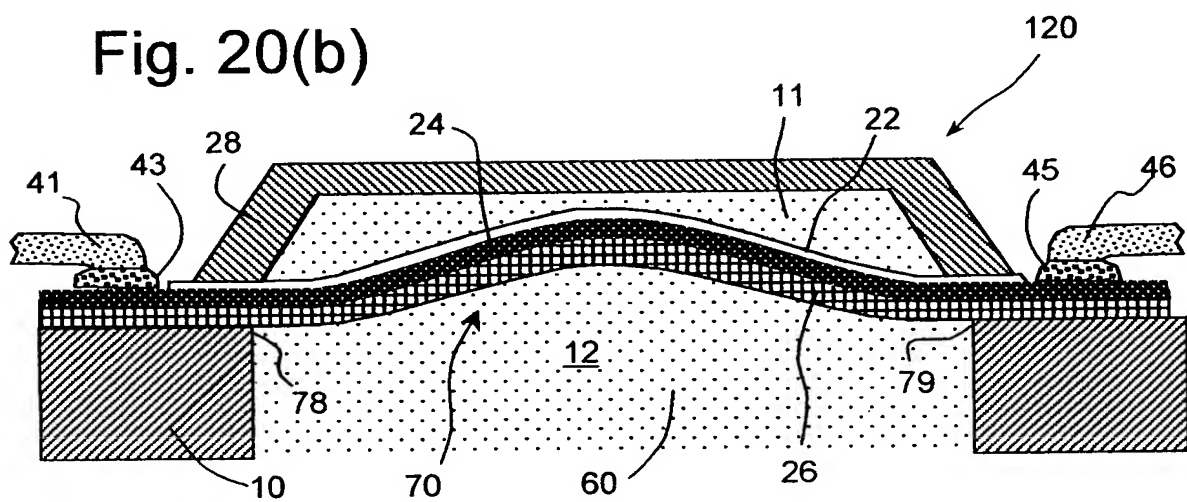


Fig. 20(c)

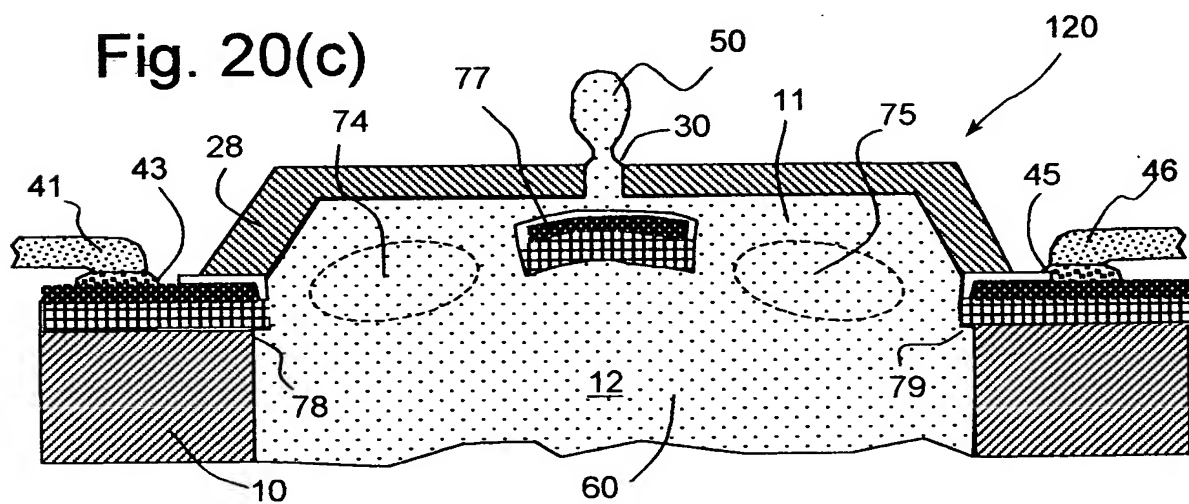


Fig. 21(a)

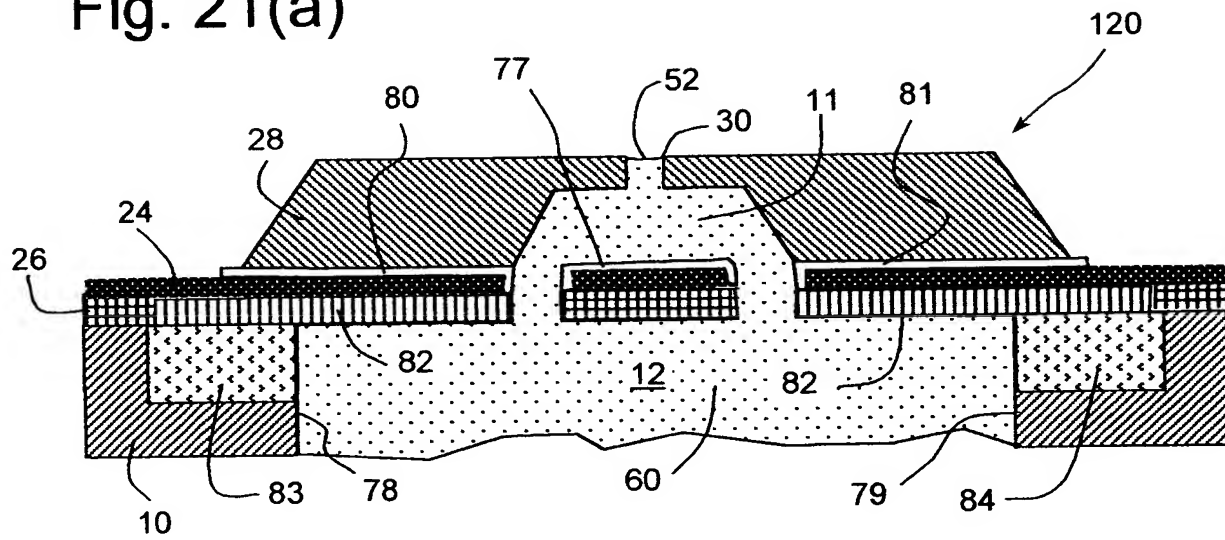
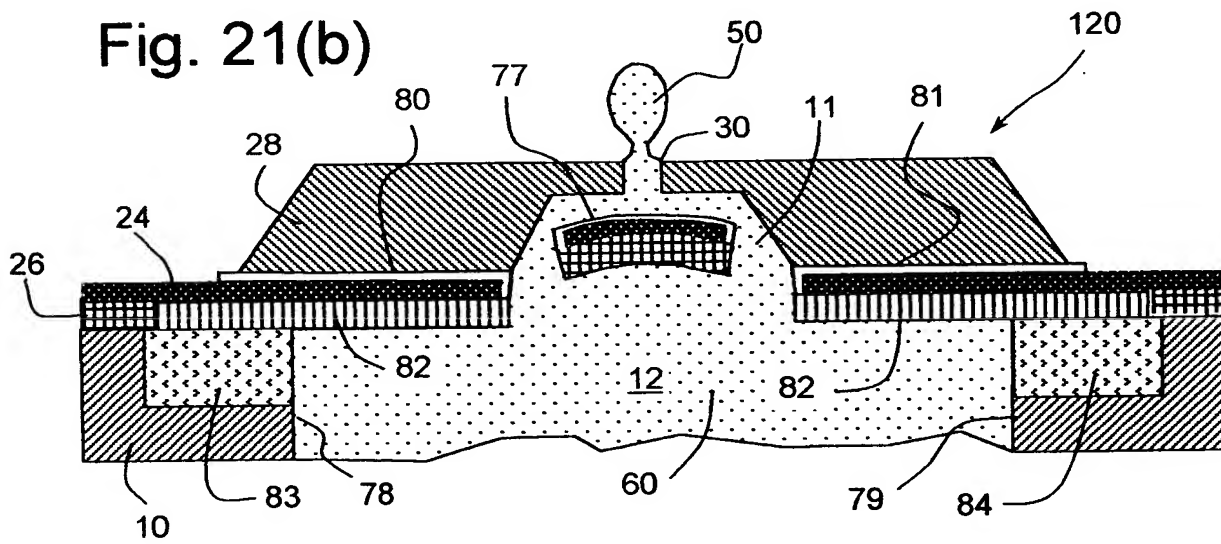


Fig. 21(b)



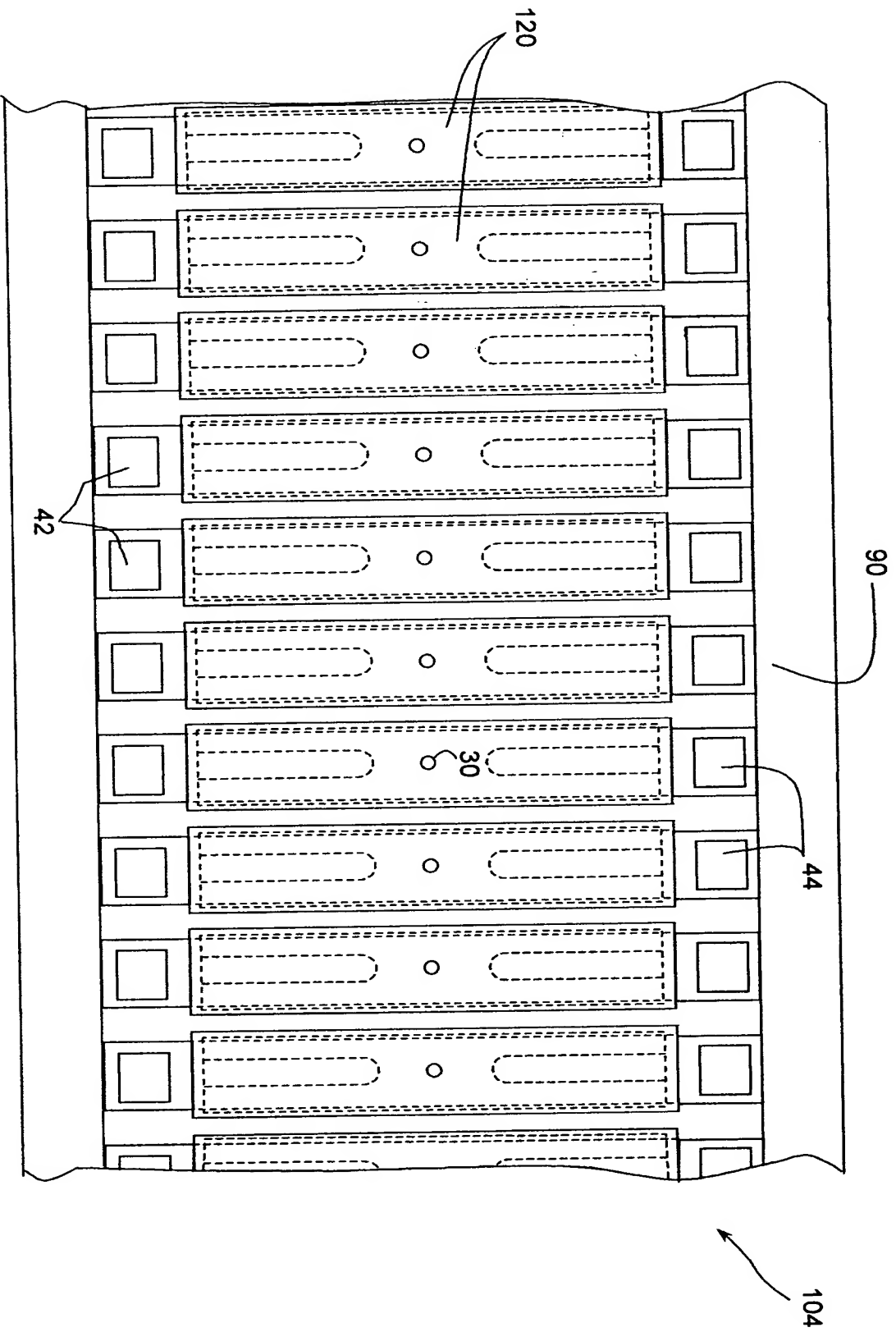


Fig. 22